DASHEVSKIY, L.W.

Characteristics of the behavior of dynamic systems near the limits of stability. Sbor.trud. Inst. elektrotekh.AH URSR no.13:35-41 '56. (MLRA 9:10)

(Blectric power distribution)

· (文文和宗经司) : 其 直接 · 安尔古代的原理 经现金的利用物的制度证据 · 网络特别在第三个一

DASHEVSKIY, L. M.

"Design of Symmetrical Flip-Flops for Maximum Reliability."

x The author explains the design procedure and derives and discusses the necessary formulas. Technical data are provided. There are 6 references, of which 4 are English and 2 Soviet.

Voprosy vyschislitel'noy matematiki i tekhniki (problems in Computor Mathematics spx and Technique) Kiev, Isd-vo AH Ukr SSR, 1958, 97 pp. (Sbornik trudov, vyp 3)

This collection of articles issued by the computer Center of Ukr SSR Acad Sci is intended for scientists and engineers in the field of computer mathematics and techniques. The collection is devoted to the programming of mathematical problems on electronic computers and to the design of units and components of these machines.

DASEEVSKIY, L. N. and POGREBINSKIY, S. B.

"A Variant of the Standard Parallel-Action Arithmetic Unit."

The authors describe a variant of a standard arithmetic unit, which they recommend for use in electronic automation systems where basic arithmetical and logical operations corresponding to certain established requirements must be performed. According to the authors this variant system provides features of universality, simplicity of the logical system, reliability, high speed, and low purchase cost. There are 8 references, of which 7 are Soviet and 1 German.

Voprosy vyschislitel'noy matematiki i tekhniki (Problems in Computor Mathematics and Technique) Kiev, Isd-vo AW Ukr SSR, 1958, 97 pp. (Sbornik trudov, vyp. 3)

This collection of articles, issured by the Computor Center of UKr SSR Acad Sci is intended for scientists and engineers in the field of computor mathematics and techniques. The collection is devoted to the programming of mathematical problems on electronic computers and to the design of units and components of these machines.

16,6800

8/112/60/000/05/10/023

Translation from: Referativnyy zhurnal. Elektrotekhnika. 1960, No. 5, p. 323, # 4.4320

AUTHORS:

Dashevskiy, L. N., Pogrebinskiy, S. B.

TITLE:

On one Circuit of a Standard Parallel Arithmetic Unit

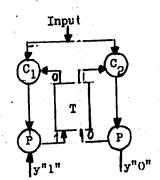
PERIODICAL: Sb. tr. Vychisl. tsentra. AN UkrSSR. 1958, No. 3, pp. 32-44

TEXT: A detailed description is given of logical and structural circuits of standard parallel arithmetic units. It is presumed that the developed standard units will be employed extensively in a number of electronic automation systems. The following requirements had to be considered when designing the standard units: universality in performing arithmetic and logical operations, simplicity of the logical circuits, reliability, high-speed action, low costs. The following points were taken as fundamental parameters and characteristics of arithmetic elements: binary computing system, fixed point, word length of 16-20 digits, 300 kc synchronizing pulse frequency for the tube variant, 300 kc for the junction transistor variant. The basic element of arithmetic units is the flip-flop (see figure), distinguishing itself by the absence of a differentiating circuit

Card 1/3

s/112/60/000/05/10/023

On one Circuit of a Standard Parallel Arithmetic Unit



on the carry forming channel. The transition of the flip-flop to a new state is effected with the aid of gating circuits (C<sub>1</sub>, C<sub>2</sub>) and the start pulse. The gating circuits are controlled by potential outputs of the flip-flop in such a way that the start pulse can pass one of the inputs only. In order to obtain a steady start, the input pulse should be shorter than the transient process time of the very flip-flop. The circuits P represent logical "or" gates with the aid of which the flip-flop returns to the zero state or a recording of 1 is effected. The authors show and describe the logical circuits of the register and the

adder. A prouliarity of the adder is the addition of numbers in two cycles and the absence of memory elements. The authors investigate the general circuit diagrams of arithmetic units and also the structural circuit diagram of one digit of the arithmetic unit. The suggested circuits ensure the execution of basic operations and possess the following special features: a) for multiplication and division operations, shift and addition are effected in different registers, which makes

Card 2/3

S/112/60/000/05/10/023

On one Circuii of a Standard Parallel Arithmetic Unit

it possible t: combine these actions and to reduce the overall time; b) there are no shifts in the adder, which ensures an increase in operating frequency; c) the absence of memory elements. An 8-digit model of an arithmetic unit with an operating frequency of 200 kc has been developed, it performs 20,000 multiplication operations per second. Static flip-flops with 6 ll (6NIP) tubes and pulse potential "cr" gates are used in the model. One digit of the unit contains tubes, 40 dindes and 22 pulse flip-flops. The authors briefly describe the principles of construction of a single-program control machine. There are 8

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S/103/60/021/06/11/016 B012/B054

AUTHORS:

Glushkov, V. M., Dashevskiy, L. N., Nikitin, A. I. (Kiyev)

TITLE:

Utilization of Electron Computers for the Automation of

the Bessemer Process

PERIODICAL:

Avtomatika i telemekhanika, 1960, Vol. 21, No. 6,

pp. 877 - 883

TEXT: The authors describe the automation of the control and regulation of the Bessemer process achieved after long experimental investigations which were carried out by the Dneprodzerzhinskiy vecherniy metallurgicheskiy institut (Dneprodzerzhinsk Evening Institute of Metallurgy) and the zavod im. Dzerzhinskogo (Works imeni Dzerzhinskiy). The latter two establishments investigated the available nonautomatic controlling methods of the Bessemer process, and worked out new methods suitable for automation on the basis of high-speed electron computers. A system has to be worked out by which it is possible to interrupt the blowing of rail steel at a carbon content of 0.48 - 0.58%. In consideration of the burning rate of carbon of 0.007 - 0.008% per second, the instant of

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. ५७% (१९४८)मः १८५ ३ वर्षस्य १४४।सम्बद्धानं <mark>च्यानसम्बद्धानं प्रशास्त्रसम्</mark>

Utilization of Electron Computers for the Automation of the Bessemer Process

S/103/60/021/06/11/016 B012/B054

converter tipping must be predicted with an accuracy of  $\pm$  5 seconds. The authors describe the methods of determining this instant used on the basis of theoretical and practical investigations. This instant is predicted on the basis of information received with the use of methods of mathematical statistics. The information received by all methods for the determination of the instant is taken into account. Work for the automation of the Bessemer process was performed in two stages: First, the information apparatus was designed, mounted, and taken into operation at the Works imeni Dzerzhinskiy; it was automatically connected with the transmitters, and automatically started and stopped; in the second stage, a digital control machine was developed. This recording digital apparatus was worked out by the Vychislitel'nyy tsentr AN USSR (Computation Center of the AS UkrSSR). It is described, and its mode of operation is explained. The authors describe the operation conditions of this plant, and its construction and principal elements. It was installed at the Works imeni Dzerzhinskiy in March 1960. At present, the data obtained from this plant are being evaluated mathematically together with the data of chemical analyses, and a program for the controlling machine is set up. There are 2 figures.

Card 2/2

DASHEVSKIY L. N.

35204

S/696/61/002/000/002/009 D299/D302

9,7100

AUTHORS:

Dashevs kvv. L.N., Pohrebins kyy, S.B. and Shkabara, K.O.

TITLE:

Basic diagram and design principles of the digital computer

"Kyyżv"

SOURCE:

Akademiya nauk Ukrayina koyi RSR. Obchyslyuval nyy tsentra

Zbirnyk prats z obchyslyuval noyi matematyky i tekhniky.

v. 2, 1961, 8-14

TEXT: The digital computer "Kyyiv", designed at the Computation Center of the Academy of Sciences of the UkrRSR, is a general-purpose mathine of intermediate speed. In designing the computer, particular attention was given to high reliability, simplicity of logical circuits, compactness and simplicity in handling it; sufficient speed and flexibility in solving various types of problems were also provided for. The operational principle of the computer is asynchronous; its various units are autonomous, each operating at its optimal frequency. The autonomous working of the various units makes it possible to carry out the required

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Basic diagram and design ...

operations in parallel, and not in series. Such an independent system of operation of the various units has the following advantages: The connection between the units is simplified; each unit is independent and can be sasily checked and repaired; this facilitates the plant manufacture of the units. The units are integrated and can be replaced individually without assessitating reconstruction of the satire computer; theraby it becomes possible to design modified versions of the computer, having different fastness and storing capacity. The main counting and control slament of the computer is the symmetrical flip-flop of triods type 68/177 (6NIP). The counters operate by means of logical elements which are centrolled by the anode veltage of the flip-flops; this ensures reliability of operation. The central system is based on the voltagepulse method, whereby to some of the inputs of the logical elements the central weltages are applied, and to the others the pulse signals. The principal legical element is a diede-transformer pulse-weltage device. The limiting operating frequency of the principal units is 500-600 kc.; the amplifiers and the blocking generators have a frequency of 500 kc.,

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Basic diagram and design ...

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at a pulse duration of 0.25-0.35 microseconds. The flip-flops were reliable to within 10%. The average speed of performing three-address operations was 5000-8000 op/sec; addition took 8 microsec., multiplication --200 microsec.; (these are minimum figures). With group operations, the speed of the computer does not decrease. The basic diagram of the computer is shown; its main units are the arithmetical unit, the internal-and external memory units, the control unit and the input- and output units. The operation of the computer is described. The various units are coordinated by the control system. The principal control desk regulates the (a.c.-) current supply, the start and stop of the computer; it control possible failures and facilitates the formulation of the problems to be solved. The computer has a total of about 2300 tubes. It consumes 25 kw and occupies a total area of 70 m<sup>2</sup>. There is he figure.

ıX

Card 3/3

8/044/62/000/009/065/069 A060/A000

9,7000 AUTHOR:

Dashevs'kiy, L.N.

TITLE:

On the problem of improving the reliability of electronic com-

puters

PERIODICAL: Referativnyy zhurnal, Matematika, no. 9, 1962, 60, abstract 9V379 ("Zb. prats' z obchysl. matem. 1 tekhn." T. 2. Kyiv, AN URSR,

1961, 87 - 95; Ukrainian; Russian summary)

Some considerations are cited relating to the improvement of the reliability of electronic computers. Main attention is drawn to raising the reliability of components by a sufficiently rigorous calculation of their parameters. The methods of analyzing certain components (inverters, cathode followers) for maximum reliability are set forth. A general criterion is formulated for the reliability of circuits with voltage coupling, characterizing the limiting admissible deviations of the circuit parameters from the nominal values under the condition of retaining the operating schedules within the boundaries of the linear segments of the characteristics. Examples are given of cal-

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\$/044/62/000/010/041/042 B158/B102

AUTHORS:

Dashevskiy, L. N., Pogrebins'kiy, S. B., Shkabara, K. O.

TITLE:

Structure scheme and basic constructional principles of a

"Kiyev" automatic digital device

PERIODICAL:

Referativnyy zhurnal. Matematika, no. 10, 1962, 66-67, abstract 10V355 (Zb. prats' z obchisl. matem. i tekhn. v. 2.

Kiyev, AN USSR, 1961, 8-15 [Ukr.; summary in Russ.])

TEXT: The "Kiyev" automatic digital device designed at the Vychislitel'nyy tsentr AN USSR (Computer Center of AS UkrSSR) is a universal mean velocity machine for solving a wide range of mathematical problems. The machine is constructed on the asynchronous principle with the individual components autonomized and operating at optimum frequency, which can easily be brought up to date by replacing one or more of these. The work of the individual components is coordinated by a control system provided, with starter devices which generate impulses to control information processing on receipt of signals from the components concerned indicating that they have completed the processing of information previously accepted by them. Pulse-potential

Card 1/2

KOPYTOV, V.F., doktor tekhn. nauk, otv. red.; VESELOV, V.V., kand. khim. nauk, red.; YERINOV, A.Ye., kand. tekhn. nauk, red.; TISHCHENKO, A.T., kand. tekhn. nauk, red.; DASHEVSKIY, L.N., kand. tekhn. nauk, red.; CHEGLIKOV, A.T., kand. tekhn. nauk, red.; SEMENKOVSKAYA, P.T., kand. tekhn. nauk, red.; YEREMENKO, A.S., kand. tekhn. nauk, red.; DYBAN, Ye.P., kand. tekhn. nauk, red.; FEDOROV, V.I., kand. tekhn. nauk, red.; POL'SKIY, N.I., kand. fiz.-mat. nauk, red.

[Transactions of the Second Heat Engineering Conference of Young Research Workers] Trudy vtorci teplotekhnicheskoi konferentsii molodykh issledovatelei. Kiev, Izd-vo AN USSR, 1963. 278 p. (MIRA 17:6)

1. Teplotekimicheskaya konferentsiya molodykh issledovateley, 2, 1963. 2. Chlen-korrespondent AN Ukr.SSR (for Kopytov).

APPROVED FOR RELEASE: 08/25/2000 CIA-RDP86-00513R000509720016-1"

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ACCESSION NR AM5006619

BOOK EXPLOITATION

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Dashevskiv, Lev Naumovich (Candidate of Technical Sciences); Pogrebinskiv.

55. Onon Beniaminovich (Engineer); Shkabara, YEkaterina Alekseyevna

(Candidate of Technical Sciences)

"The "Kiev" computer; design and application (Vychislitel'naya mashina "Kiyev"; proyektirovaniye i ekspluatasiya), Kiev, Izd-vo "Tekhnika", 1964, 322 p. 111us., biblio. 4,600 copies printed.

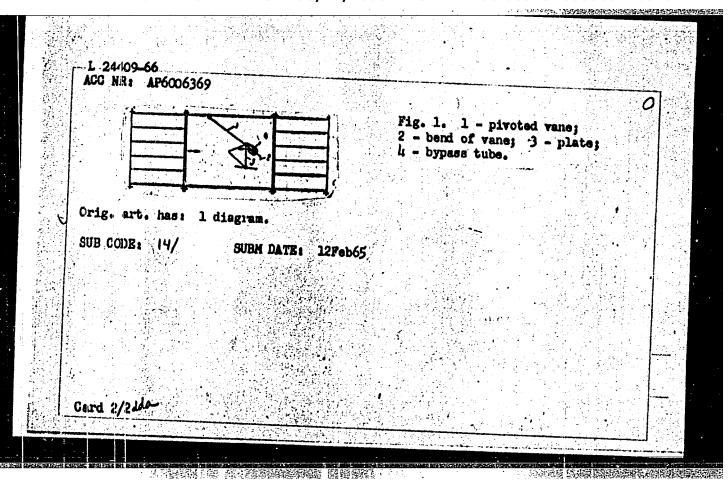
TOPIC TAGS: computer technology, digital computer KIYEV

PUNPOSE AND COVERAGE: This book collected the experience in the design and use of the asynchrous universal digital computer "Kiev". The principles of its construction and structure circuitry, the method of performing control and existence operations, and the schematics of the elements, components, and hasic units of the computer are described. The book includes the methods of alcolating and investigating the reliability of a digital computer and problems of organizing the use of large electronic digital computers. The book is intended for engineers, researchers, students in graduate students in the field of computer technology and cybernetics and also for specialists interested in the development and use of computer and control equipment.

Card 1/2

SUBMITTED: 31 JUL 64

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	[17] 전 [17] - [2] 1일	
	AUTHORS: Chernoval, V. S.; Shcherba, N. U.; Frelin, N. V.; Dashevskiy, L. N.; Kolyada, I. A.; Gudrit, Ye. R.; Fediv. V. A.; Ivanovskiy, E. N.; Hasur, P. A.;	
	Yaskevich, L. Ye.	
	ORG: none	
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	TITLE: Streamline flow meter. Class 42, No. 178125 [announced by Gas Institute, AN UkrSSR (Institut gaza AN UkrSSR)]	
	SOURCE: Izobreteniya, promyshlennyye obraztsy, tovarnyye znaki, no. 2, 1966, 100	변수). 신청 신청
; (   ; ( )	TOPIC TAGS: flow meter, streamline flow	
	ABSTRACT: This Author Certificate presents a streamline flow meter containing a	
	sensing element in the form of a pivoted vane and jet rectifiers mounted in front of and behind the vane (see Fig. 1). To decrease vibrations, the pivoted vane	
	has a bend in the side opposite the flow direction. A plate whose center of	
	gravity is displaced toward the free end of the vane is hinged to the vane. There is also a bypass tube connecting the front and back of the vane.	
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3,	Card 1/2 UDC: 532.574.27	



ACC NR. AP6036065

(A, N)

SOURCE CODE: UR/0432/66/000/005/0041/0943

AUTHOR: Dashevskiv, L. N. (Candidate of technical sciences); Pleskonos, A. K.; Lazarkevich, I. A.; Hedvedev, R. B.

ORG: none

TITLE: Multiple point device in a system for the digital registration of parameters

SOURCE: Mekhanizatsiya i avtomatizatsiya upravleniya, no. 5, 1966, 41-43

TOPIC TAGS: computer input unit, computer research, analog digital conversion

ABSTRACT: A breadboard model of a system for the digital recording of parameters, including single and multiple point secondary devices, is briefly described. The multiple point devices do not have a continuous time relationship between the sliding element of the rheochord and the value of the parameter. The correspondence between the voltage picked up from the rheochord and the variable parameter occurs when the carriage is lowered on the chart paper of the device. A block diagram of the system is presented and discussed. Orig. art. has: 3 figures.

SUB CODE: 09/

SUBM DATE: none

UDC: 681.14:62-50

Card 1/1

MOYZHES, V., insh.; PUEZON, S., insh.; DASHEVSKIY, M., insh.

Using machinery in erecting a blast furnace. Stroitel' no.12:

(MIRA 12:1)

(Blast furnaces)

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# DASHEVSKIY, M.

Construction of a cold-rolling mill. Prom. stroi. i inzh. soor. 5 no.2: 3-7 Mr-Ap \*63. (MIRA 16:4)

l. Nachal'nik Donetskogo otdela Ukrainskogo gosudarstvennogo proyektnogo instituta po proyektirovaniyu, issledovaniyu i ispytaniyu stal'nykh konstruktsiy i mostov.

(Zhdanov-Rolling mills-Design and construction)

### DASHEVSKIY, M.

Accounting has been mechanized. Fin.SSSR 37 no.2:62-63 F \*63. 1. Glavnyy bukhgalter upravleniya gosudarstvennykh trudovykh sberegatel'nykh kass i gosudarstvennogo kredita Moldavskoy SSR.

(Moldavia—Savings banks—Accounting)

(Machine accounting)

### "APPROVED FOR RELEASE: 08/25/2000

#### CIA-RDP86-00513R000509720016-1

DASHEVSKIY, M.I.

USSR/Physical Chemistry - Kinetics, Combustion, Explosions,

5-9

Topochemistry, Catalysis.

Abs Jour

: Referat Zhur - Khimiya, No 1, 1958, 498

Author

: A.M. Rubinshteyn, M.I. Dashevskiy, N.A. Pribytkova.

Inst

: Academy of Sciences of USSR.

Title

: Application of Method of Ultrathin Sections to Electronic

Microscopy of Catalysts.

Orig Pub

: Izv. AN SSSR. Otd khim. n., 1957, No 4, 431-435

Abstract

: The authors polymerize specimens in a mixture of methyland butylmethacrylates (1:3) and make sections less than 0.01 thick with a specially constructed microtome from blocks prepared in the above manner. These sections are used for electron-microscopic study of

highly dispersed catalysts.

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Card 1/1

# DASHEVSKIY, M.I.

UND-5 ultramicrotome. Priroda 51 no.5:104-107 My 162. (MIRA 15:5) 1. Institut organicheskoy khimii im. N.D.Zelinskogo AN SSSR, (Microtome)

APPROVED FOR RELEASE: 08/25/2000 CIA-RDP86-00513R000509720016-1"

PECHKOVSKAYA, K.A.; PAVLOVA, I.P.; SINYAYEVA, O.A.; DASHEVSKIY, M.I.

Use of electron microscopy for evaluating the distribution of carbon black in rubber compounds. Zav.lab. 29 no.8:968-970 163. (MIRA 16:9)

1. Nauchno-issledovatel'skiy institut shinnoy promyshlennosti.
(Rubber) (Carbon black) (Electron microscopy)

DASHEVSKIY, M.

USSR/Chemistry - Rubber Butadiene Rubber

Sep/Oct 48

"Structure and Properties of Filled Rubber Mixtures: III, Mixtures of Sodium Butadiene Rubber With Channel Black," B. Dogadkin, D. Pechkovskaya, M. Dashevskiy, Sci Res Inst of Tire Ind, 12 pp

"Kolloid Zhur" Vol X, No 5

Ukhtinskiy channel black as a filler for sodium butadiene rubber was examined in concentrations of less than 20, 20 - 40% in relation to amount of rubber. Found that in concentration of 20 - 40% of the black, structural arrangements were effected (threads and small chains). This did not occur for lower concentrations; in concentrations of 40 and above, surplus black did not form additional structural groups but was merely dispersed between them. Rubrax and sulfur retarded process, but mercaptobenzothiazole accentuated it. Stearic acid had no noticeable effect. In all degrees of concentration of channel black, rubber remained a continuous-phase system. Submitted 3 Jan 48.

FA 2/50T59

TO THE WILL IN A PROPERTY OF

S/026/62/000/005/007/010 D036/D113

AUTHOR:

Dashevskiy, M.I.

TITLE:

The UMD-5 ultramicrotome

PERIODICAL: Priroda, no. 5, 1962, 104-107

The YMI -5 (UMD-5) ultramicrotome, designed and produced at the Institut organicheskoy khimii im. N.D. Zelinskogo Akademii nauk SSSR (Institute of Organic Chemistry im. N.D. Zelinskiy, Academy of Sciences USSR), is intended for obtaining ultrathin (50 - 800 Å) and thin (1/k) sections of various substances, including polymers, catalysts and soft minerals for subsequent examination under an electron microscope. It has a rocking sample-holder and thermal feed of the sample towards the cutter. Microphotographs made with the aid of the ultramicrotome are included. There are 3 figures.

ASSOCIATION:

Institut organicheskoy khimii im. N.D. Zelińskogo AN SSSR (Moskva) (Institute of Organic Chemistry im. N.D.Zelińskiy of the AS USSR Moscow)

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AUTHOR: Dashevskiy, M. L.	(Moscow); Liptser, R. Sh. (Moscow)
ORG: none	
TITLE: Simulation of stechas	tic differential equations connected with the problem of
"disharmony" on an analog con	mputer
SOURCE: Avtomatika i telemo	ekhanika, no. 4, 1966, 142–150
TOPIC TAGS: random noise a process, signal detection, sig	signal, analog computer, computer application, stochastic mal noise separation
noise and the problem of control realization of the linear and n has been largely reduced in reating in real time and receiving matical nature which are encountries.	is with the problem of signal detection against a background of roll on the basis of incomplete data. A proper device for the ionlinear stochastic differential equations, to which this problem ecent times, might be a continuous-acting analog computer opening a signal-noise mixture. The difficulties of a purely mathemulated in the simulation of such equations are pointed out and a suggested. Methods for the simulation of controlled diffusions proposed, and the results of the simulation of a random process.
Cord 1/3	UDC: 621.391.161:681.142.33

#### L 43709-66

#### ACC NR: AP6023669

involving the "disharmony" problem are discussed. A process  $\eta_*$ , which is the sum of the useful signal and "white" Gaussian noise, is observed. The useful signal is a Markovian process with two states 0 and 1, for which a transition is possible at a random moment of time 0 only from state 0 to state 1; i.e., the random process satisfies the stochastic differential おかいかいからか equation

$$\forall d\eta_t = \chi(t-\theta)dt + d\xi_t,$$

where

$$\chi(t-\theta) = \begin{cases} 0, & t < \theta, \\ 1, & t \ge \theta, \end{cases}$$

 $\xi_t$  is the Wiener process,  $M\Delta \xi_t = 0$ ,  $D\Delta \xi_t = \Delta t$ . In addition, it is known that the random quantity 0 has the following a priori distribution

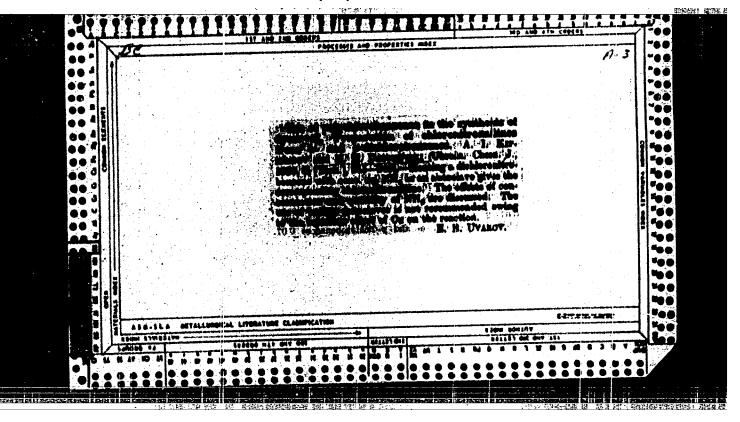
$$P(\theta > t | \theta > 0) = e^{-\lambda t}, \quad P(\theta = 0) = \pi.$$

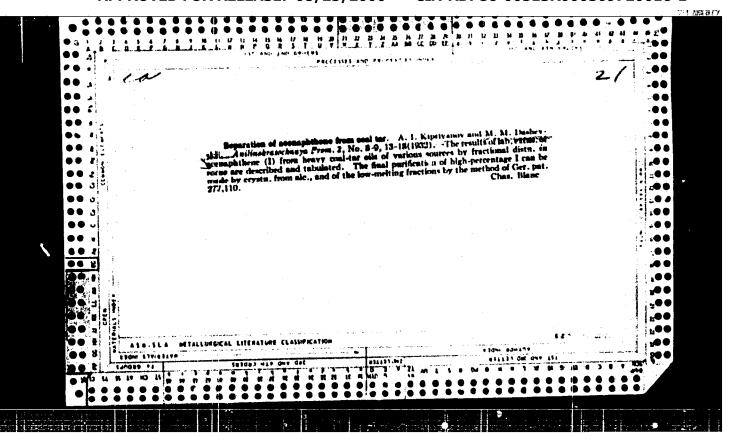
Here  $\pi$  and  $\lambda$  are known constants.

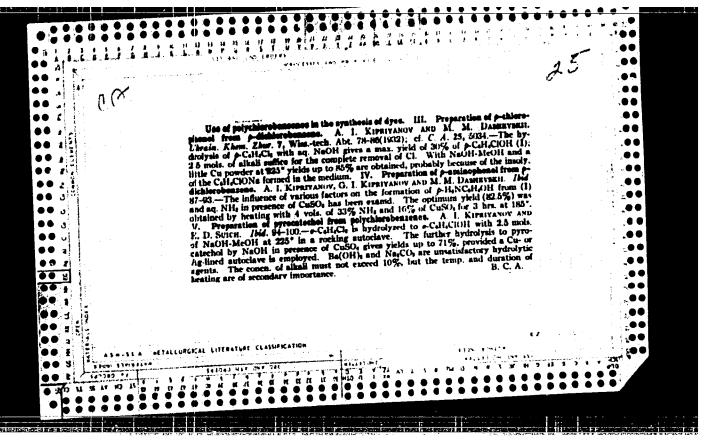
The problem is to establish, for a given probability of false alarm  $\omega = P(\nu < \theta)$  ( $\nu = P(\nu < \theta)$ ) moment at which the slarm signal is activated) and within a mean-minimal time, the fact of a transition by the useful signal from 0 to 1; i.e., to minimize the mathematical expectancy

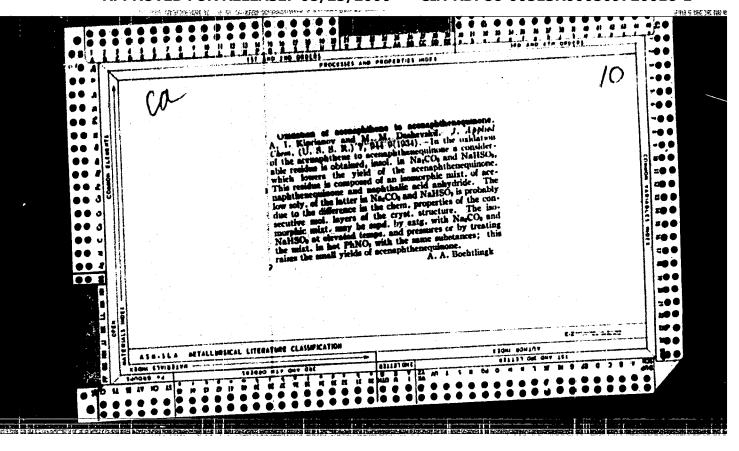
**Card** 2/3

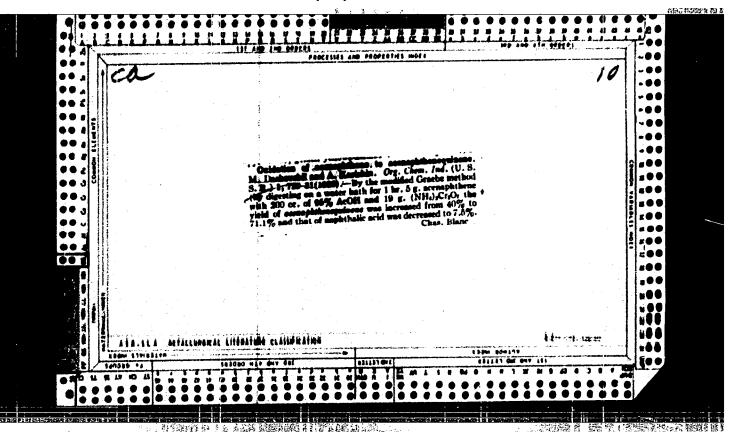
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		$\tau = M(\nu - 0)\nu \geqslant 0).$		
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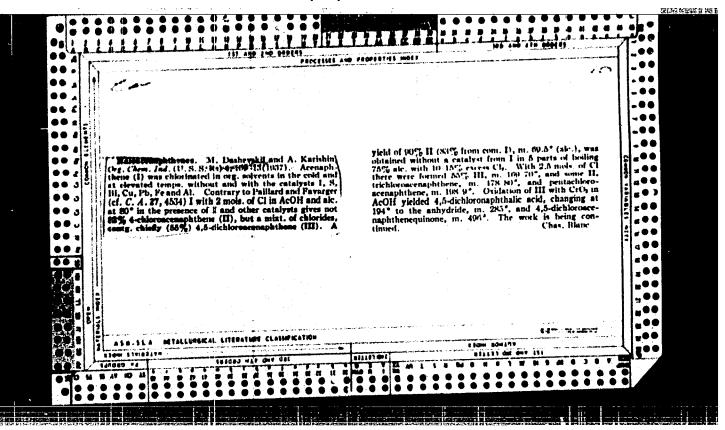




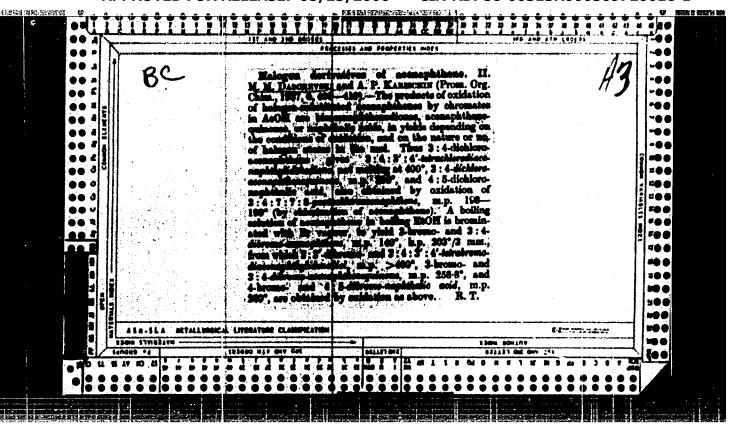




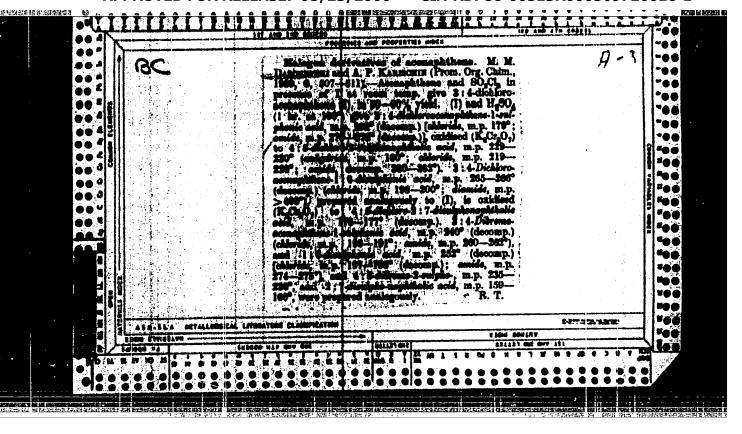


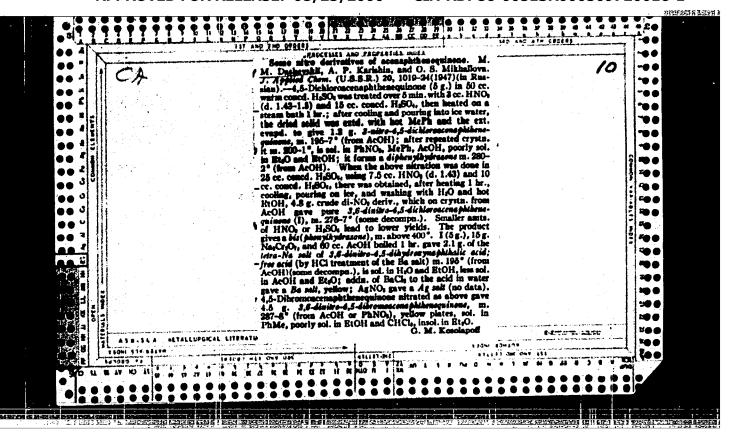


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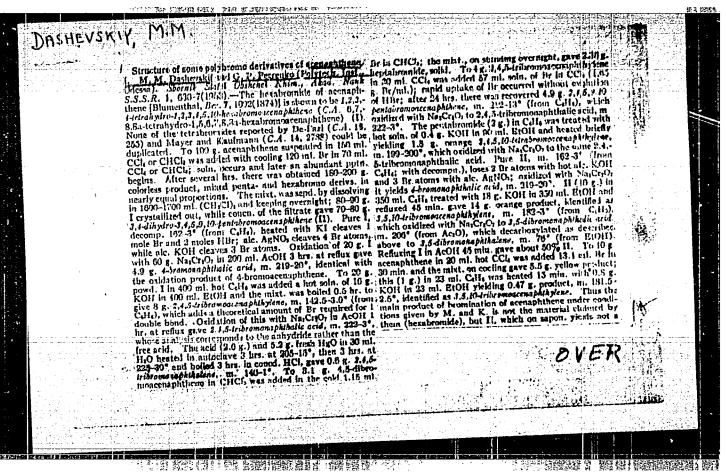


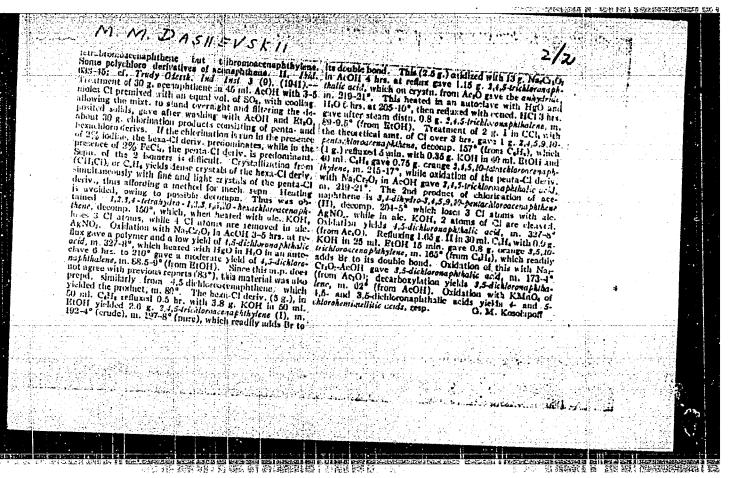
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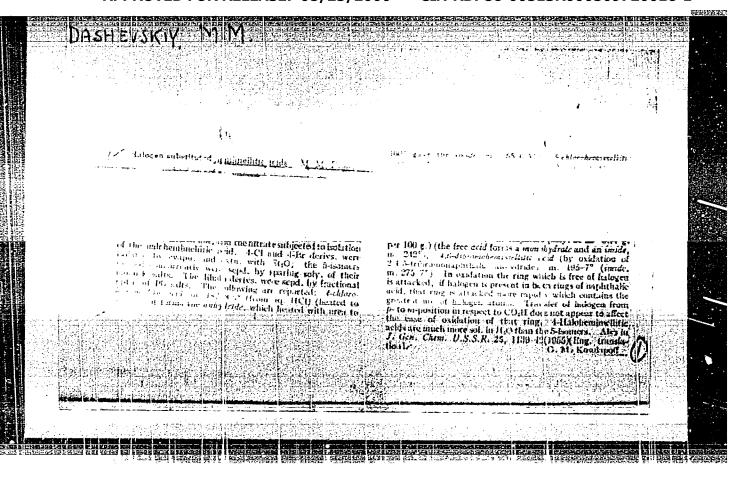


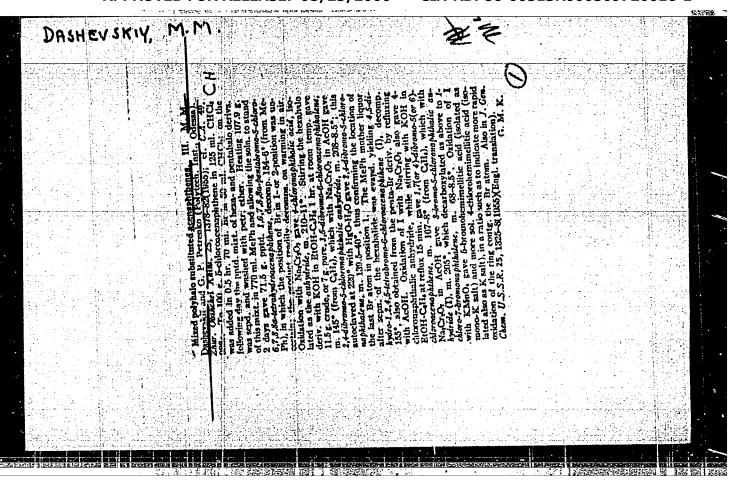
DASHERVSKIY, M. M., and PETRENKO, G. P.

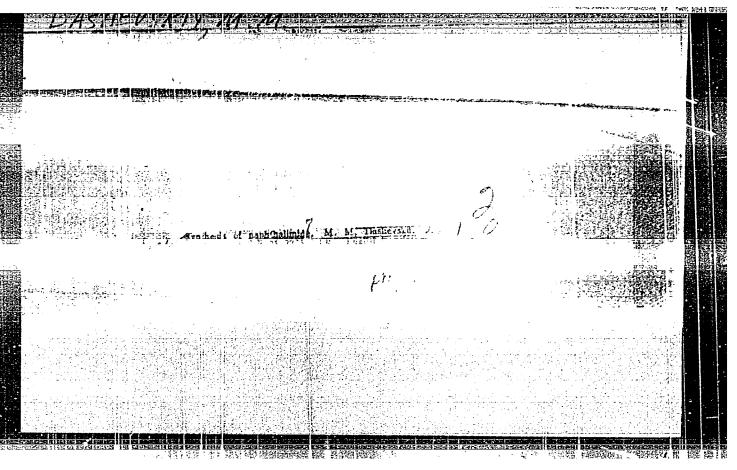
On Some Polychloro Derivatives of Acenaphthene. II. page 638. Sbornik statey po obshchey khimii (Collection of Papers on General Chemistry), Vol 1, Moscow-Leningrad, 1953, pages 762-766.

Odessa Polytechnic Inst.

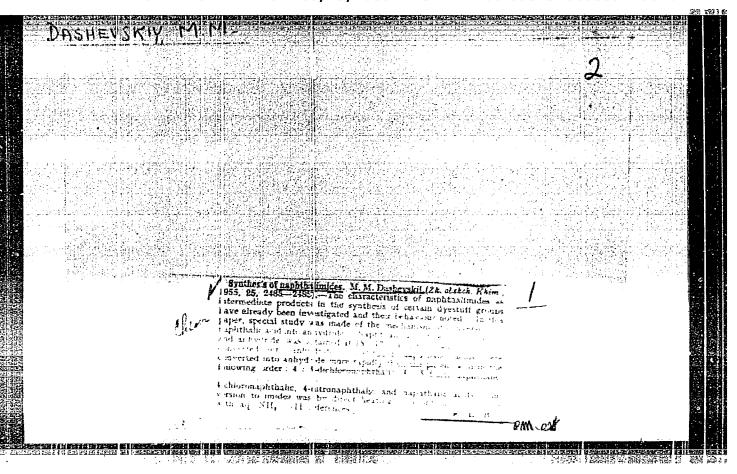
USSR/Chemistry - Organic chemistry Card 1/1 Pub. 116 - 17/30 Authors Dashevskiy, M. M., and Petrenko, G. P. About 4,5-dichloroacenaphthene and its oxidation products Title Pariodical : Ukr. khim. zhur. 21/3, 370-372, June 1955 Abstract : A new method for the oxidation of 4,5-dichloroacenaphthene into 4,5-dichloronaphthalic acid with a yield of 80 - 83% is briefly described. It was proven experimentally that the chlorination of acenaphthene with sulfuryl chloride in the presence of an aluminum chloride catalyst yields up to 75% of 4,5-dichloroacenaphthene plus small amounts of monochloroacenaphthene and tars. It was established that the yield of 4,5-dichloroacenaphthenequinone does not exceed 52% of the theoretical. Four USSR references (1934-1952). Institution : Polytechnical Inst., Odessa Submitted : January 19, 1955







"APPROVED FOR RELEASE: 08/25/2000 CIA-RDP86-00513R000509720016-1



5 (3) AUTHORS:	Dashevskiy, M. M., Petrenko, G. P. SOV/75-14-3-26/29
TITLE:	Quantitative Determination of Acenaphthylene (Kolichestvennoye opredeleniye atsenaftilena)
PERIODICAL:	Zhurnal analiticheskoy khimii, 1959, Vol 14, Nr 3, pr 375-377 (USSR)
ABSTRACT:	The authors investigated several methods which are based either on the unsaturated constitution of the accmaphthylene or on its intense yellow coloration without having obtained satisfactory results. Finally a gravimetric method was found which is characterized by the fact that accmaphthylene forms a sparingly soluble polymer under the influence of strong acids (sulfuric acid with glacial acetic acid). Table 1 presents the determination results for mixtures of accmaphthylene and accmaphthene. The results which are not quite precise can be corrected by means of a calibration curve when strictly proceeding according to the analysis directions. Simpler is the colorimetric method in which the accmaphthylene is distilled rapidly in low absolute pressure (in order to avoid resinification) and investigated photometrically in the monochromator UM-2. A figure shows the

Quantitative Determination of Acenaphthylene

SOV/75-14-3-26/29

dependence of the optical density on the concentration of the acenaphthylene. Table 2 presents the determination results which show a maximum error of 1 %. There are 1 figure, 2 tables, and 5 references, 2 of which are Soviet.

ASSOCIATION:

Odesskiy politekhnicheskiy institut (Odessa Polytechnical

SUBMITTED:

March 7, 1958

Card 2/2.

sov/80-32-5-34/52

5(3)

AUTHORS:

Petrenko, G.P., Dashevskiy, M.M.

TITLE:

The Oxidation of Acenaphthene to Naphthalic Anhydride

PERIODICAL:

Zhurnal prikladnoy khimii, 1959, Vol 32, Nr 5, pp 1126-1132 (USSR)

ABSTRACT:

The vapor-phase oxidation of acenaphthene to naphthalic anhydride is studied here. The oxidation was carried out by air at 320 - 435°C over vanadium catalysts and manganese dioxide. Vanadium pentoxide as catalyst produces a mixture of acenaphthilene with unreacted acenaphthene. At an increased air supply naphthalic anhydride may be present to the maximum amount of 29%. The addition of potassium sulfate to the catalyst raises its activity and with the increase of the temperature the yield of naphthalic anhydride rises sharply. Naphthalic anhydride is the principal product of the reaction, if the air supply is sufficient. The oxidation of acenaphthene over manganese peroxide leads to a yield of 28 - 30% acenaphthilene at 325°C. The highest yield of naphthalic anhydride is obtained with a catalyst of iron vanadate with potassium sulfate at 350 - 370°C and a volume ratio acenaphthene: air = 1:100. The time of contact is 2.9 sec. The yield of anhydride is 75 - 80% of the theoretical.

Card 1/2

The Oxidation of Acenaphthene to Naphthalic Anhydride

sov/80-32-5-34/52

There are 3 graphs, 2 tables, 1 diagram and 16 references, 1 of which is Soviet, 5 American, 4 English, 3 German, 1 French, 1 Swiss and 1 Italian.

SUBMITTED:

January 8, 1958

Card 2/2

B/079/60/030/04/49/080 B001/B002

AUTHOR:

1 Same

Dashevskiy, M. M.

TITLE:

Oxidation of 4-Mitroacenaphthene Into Nitronaphthalic Acid

PERIODICAL: Zhurnal obshchey khimii, 1960, Vol. 30, No. 4, pp. 1271-1274

TEXT: In the present paper the author describe the possibility of an exidation by means of sodium bichromate (at least of certain organic compounds) in a solution of hydrochloric acid, without the separation of chlorine. In this case, the concentration of hydrochloric acid in a certain organic compound to be exidized, must not exceed a certain degree, and must be in a certain ratio to the amount of the bichromate used. This is shown here for the exidation of 4-nitroacenaphthene. The exidation of 4-nitroacenaphthene in a medium of sulfuric acid takes place very slowly, and gives rise to a low yield. In a medium containing hydrochloride, exidation takes place quickly and under easy conditions, without resinification and combustion. The yield of 4-nitroacenaphthalic acid was 80-85%. The amount of hydrochloric acid must not exceed 5 moles of hydrogen chloride per 1 mole of sodium bichromate, while the concentration of hydrochloric acid must

Card 1/2

Oxidation of 4-Nitroacenaphthene Into Nitro-naphthelic Acid

S/079/60/030/04/49/080 B001/B002

not be more than 20%. Otherwise, chlorine is separated in the oxidation of hydrogen chloride. The best results were obtained in a double excess of bichromate and by vigorous mixing. There are 4 tables and 4 references, 2 of which are Soviet.

ASSOCIATION: Odesskiy politekhnicheskiy institut (Odessa Polytechnic Institute)

SUBMITTED: March 16, 1959

Card 2/2

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#### DASHEVSKIY, M.M.

Synthesis of naphthostyril. Izv. vys. ucheb. zav.; khim. i khim. tekh. 4 no. 2:232-237 161. (MIRA 14:5)

1. Odesnikiy politekhnicheskiy institut. Kafedra organicheskoy khimii.

(Naphthostyril)

25394 8/080/61/034/002/015/025 A057/A129

5 3300 AUTHORS:

Dauhevskiy, M.M., Petrenko, G.P.

TITLE:

Dehydrogenation of acenaphthene

PERIODICAL: Zhurnal Prikladnoy Khimii, v 34, no 2, 1961, 391-395

TEXT: Vapor phase dehydrogenation of acenaphthene with and without catalyst was investigated. Various diluents (nitrogen or carbon dioxide gas, steam, or aim) were used and a technically suitable catalytic method with a Zn/Al catalyst was developed giving a yield of 90% of a product with a Zn/Al catalyst was developed giving a yield of 90% of a product containing 95-98% acenaphthylene. The latter is of interest for syntheses of copolymers with special properties and thus for the production of plastics. Some of the first syntheses of acenaphthylene were made by plastics. Some of the first syntheses of acenaphthylene were made by plastics. Some of the first syntheses of acenaphthylene were made by plastics. Some of the first syntheses of acenaphthylene were made by Catalysian (Ref 10: Ber., 45, 249 (1912)), and K. Dzie-K. Dziewonski, G. Rapalski (Ref 10: Ber., 57, 1540 (1924)), while later investigations were carried out by J. Jones (Ref 13: J.Soc.Chem.Ind., 68, 225 gations were carried out by J. Jones (Ref 13: J.Soc.Chem.Ind., 68, 225)

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Dehydrogenation of acceptather.

S/080/61/034/002/015/025 A057/A129

(1949)), W. Kynaston, J. Jons (Ref 14: J.Sco.Chem.Ind., 68, 229 (1949)), and M. Kaufmann, A.F. Williams (Ref 1: J.Aprl. Chem., 1, 489 (1951)). The two last mentioned are the most important. The present dehydrogenation experiments were carried out in two series: 1. without catalyst and with various diluents at 180°C~880°C in an apparatus described in a previous paper (Ref 15: Nauchn. zap. Odenskogo politekhn. inst., (Scientific reports of the Odessa Polytechnical Institute), 16 73 (1959)) and 2. with a zino-aluminum oatalyst in a U-shapei resotur tube. In the first series it was observed that with increasing temperature the accraphthylene content increases, but also the amount of side products (acenaphthene polymers). Optimum results were obtained with parbon dioxide as diluent, 1.c., 68.3% yield of acenaphthylene. Optimum ratio of diluent/acenaphthene is 2.5 for carbon dioxids, 3.9 for nitrogen (yield 58.6%), 2.3 for steam (50.4% yield), and 5-6 for air. Without diluent reaction cocure at lower temperature with a 39.5% yield, but a considerable carbonization of the product is observed. The Zn/Al catalyst was prepared as follows: 540 g ZnO, 60 g Al203, 18 g K2SO4 and 540 ml H2O were mixed, the paste applied on a glass

Card 2/8

25394 S/080/61/034/002/015/025 A057/A129

Dehydrogenation of acenaphthene

surface (5-6 mm layer) and left to stand for 24 hrs at room temperature. Then 4-7 mm pieces were dried for 2-3 hrs at 125°C, and for 2-3 hrs at 600°C. After this the catalyst was treated for several hours with steam at the temperature of the experiment. The diagram of the device used for dehydrogenation experiments with this catalyst is presented in Fig 1. Hot water was passed through the cooler (5) to avoid obstruction of the outlet. The present authors consider it unnecessary to pass acenaphthene vapors with a corresponding diluent as it is suggested in the German patent 921989, CBI 5424 (1959). The second cooler was water-cooled. In each experiment 30 - 100 g acenaphthene were used and the duration varied from 15 - 120 min. Some of the obtained results are presented in Tab. 2. Considerable effect of temperature was observed (Fig 2). The drop in acenaphthylene content above 600°C is explained by an increase of side reactions, i.e., formation of naphthalene methylnaphthalene etc. An essential effect on dehydrogenation is exercised by the contact time. There are 2 figures, 2 tables and 17 references: 4 Scriet-bloc, 13 non-Soviet-bloc.

Card 3/8

# "APPROVED FOR RELEASE: 08/25/2000

CIA-RDP86-00513R000509720016-1

25394 3/080/61/034/002/015/025 A057/A129

Dehydrogenation of ecenaphthene

ASSOCIATION: Cdesskly polytekhnicheskiy institut (Cdessa Polytechnic Institute)

SUBMITTED 8

February 5, 1960

Card 4/8

DASHEVSKIY, M.M., kand. khim. nauk, dotsent; SHAMIS, Ye.M.

Friedel-Crafts acetylation of aromatic hydrocarbons. Nauch. zap. Od. politekh. inst. 40:83-87 '62. (MIRA 17:6)

1. Predstavlena kafedroy "Organicheskaya khimiya" Odesskogo politekhnicheskogo instituta.

DASHEVSKIY, M.M., kand. khim. nauk, dotsent; BALYKINA, Ye.P.; PUPINA, L.N.

Synthesis of -(4-acenaphthyl)-ethylamine (IV). Nauch. zap. Od. politekh. inst. 40:88-90 \*62. (MIRA 17:6)

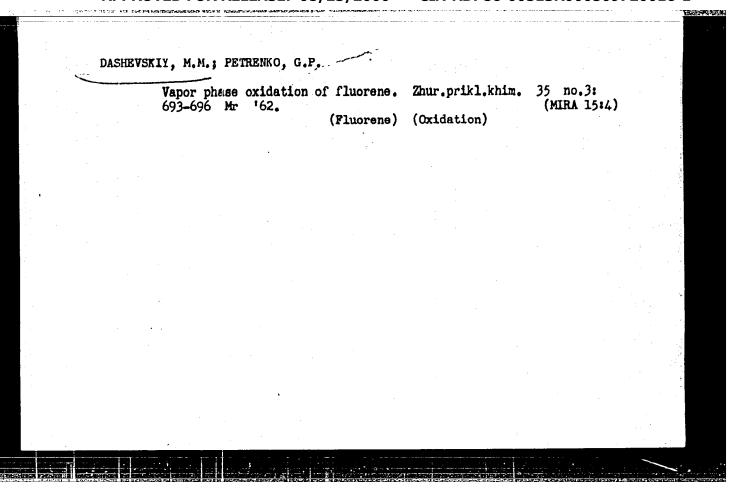
1. Predstavlena kafedroy "Organicheskaya khimiya" Odesskogo politekhnicheskogo instituta.

DASHEVSKIY, M.M., kend. khim. nauk, dotsent; TERENT'YEVA, G.N.

Nitration of some aromatic hydrocarbons. Report No.1. Nauch. zap. Od. politekh. inst. 40:91-94 '62.

(MIRA 17:6)

1. Predstavlena kafedroy "Organicheskaya khimiya" Odesskogo politekhnicheskogo instituta.



Discriptation of accomphisms. Zhur. ob. khim. 33 mo.5115731576 My '63. (MIRA 16:6)

1. Odesskiy politekhnicheskiy institut.
(Accomphisms) (Acctyl group)

DASHEVSKIY, M.M.; MALEVANNAYA, Z.P.

Structure of dipropiomylacenaphthene. Zhur. ob. khim. 33
no.5:1576-1578 My '63. (MIRA 16:6)

1. Odesskiy politekhnicheskiy institut.
(Acenaphthene)

DASHEVSKIY, M.M.; MALEVANNAYA, Z.P.

Synthesis of some acenaphthylcarbinols. Zhur.ob.khim. 34 no.1:213—216 Ja '64.

(MIRA 17:3)

1. Odesskiy politekhnicheskiy institut.

DASHEVSKIY, R.M.; SHAMIS, Ye.M.

Synthesis of some anylcarboxylic acids and diamines based on polycyclic hydrocarbons. Ukr. khlm. zhur. 30 no.9:938-941 \*64.

(MIRA 17:10)

1. Odenskly politekhnicheskiy institut.

DASHEVSKIY, M.M.; MALEVANNAYA, 7.P.

Structure of dinitroacanaphthene derivatives. Thur. org. khim.
1 no.7:1272-1276 J1 165.

(MIRA 18:11)

1. Odesskiy politekhnicheskiy institut.

MAGAZINER, Z.G.; DASHEVSKIY, M.V.

Analysis of present day conditions of pipe founding in the U.S.S.R. and in foreign countries. Izv. vys. ucheb. zav.; chern. met. 7 no.3:218-224 '64. (MIRA 17:4)

1. Moskovskiy institut stali i splavov.

DASHEVSKIY, M.V.; HAGAZINER, Z.G.

Technical and economic indices of the various methods of cast iron pressure tube casting. Izv. vys. ucheb. sav.; chern. met. 7 no.9:202-208 '64. (MIRA 17:6)

1. Moskovskiy institut stali i splavov.

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DASHENSKIY MI Ta

137-58-6-12122

Translation from: Referativnyy zhurnal, Metallurgiya, 1958, Nr 6, p 134 (USSR)

AUTHORS: Petrov, D.A., Kekua, M.G., Dashevskiy, M.Ya., Zemskov,

V.S., Petrusevich, R.L.

TITLE: Progress of Work on the Refining of Germanium by Means of

Crystallization and Achievement of Germanium Single Crystals With Longitudinally Homogeneous Properties (Razvitiye rabot po ochistke germaniya metodami kristallizatsii i polucheniye monokristallov germaniya s ravnomernymi svoystvami po

dline)

PERIODICAL: V sb.: Vopr. metallurgii i fiz. poluprovodnikov. Moscow,

AN SSSR, 1957, pp 50-58

ABSTRACT: Experiments were performed in order to investigate the

possibilities of producing single crystals with uniform longitudinal and cross-sectional distribution of impurities by means of pulling at a controlled rate as well as by pulling accompanied by constant feeding of pure Ge into the melt. The raw polycrystalline material with a  $\rho$  of 5-20 ohm/cm was purified by

means of zonal recrystallization under a vacuum of  $10^{-4}$  mm Hg, or in a stream of H<sub>2</sub>, until it exhibited a Q of 50-60

Card 1/3 ohm/cm. A high-frequency heating apparatus with three

137-58-6-12122

Progress of Work on the Refining of Germanium (cont.)

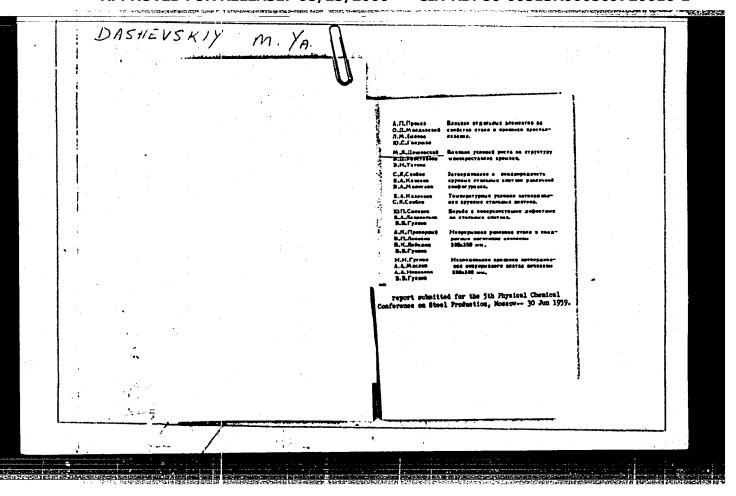
induction units moving back and forth was employed. It was found that single Ge crystals, grown by the Chokhralskiy method from purified material with a 0 of 50-60 ohm/cm in conjunction with mixing of the melt by rotating the crucible and the growing crystal, can achieve of and Tvalues of 60 ohm/cm and 1000  $\mu$  sec, respectively; if the rotation is omitted from the growth process, the  $\rho$  and the  $\tau$  amount to 25-50 ohm/cm and 200-250  $\mu$  sec, respectively. The UVM-2 apparatus, employed in the process of pulling the crystal under vacuum (10-4 mm Hg) in accordance with scheduled variations of the rate of pulling, utilizes a hydraulic raising mechanism which provides a smooth variation of the elevation rate from 0.05 to 8 mm/min in conjunction with the rotation of the crucible and the growing crystal. The Q value of grown crystals 50 mm in diameter and 180 mm long deviated from the mean value of  $\sim 40$ -60 ohm/cm, at a length of 100-150 mm, by 8.9-9.3% and was within the limits of error of measurement. It is pointed out that because of variations in conditions of crystallization only macrouniformity in the distribution of impurities can be achieved by this method. The variations were eliminated in another device which was designed for a process in which the pulling is accompanied by feeding of pure Ge into the melt. Prior to immersion into the melt, the feed ingot passes through a heating unit (composed of a quartz tube wound with W wire), while the ingot being pulled passes Card 2/3

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137-58-6-12122

Progress of Work on the Refining of Germanium (cont.)

through a water-cooled unit made of stainless steel. The process of pulling was carried out in an Ar atmosphere. The fact that the feed ingot and the growing crystal, which may rotate, were placed excentrically with respect to the axis of rotation of the crucible, contributed to a better mixing of the melt contained in the crucible. It was found that the longitudinal q fluctuations in single crystals obtained by this method did not exceed ±5%, whereas in the case of a crystal produced in this apparatus without the employment of pure Ge the scatter amounted to ± 24%. Studies of crystals with a diameter of 50 mm have revealed that the  $\rho$  was sufficiently uniform throughout the cross section of the crystal and that the diffusion-path length of minority current carriers did not deviate by more than 10-15%. The authors express the opinion that intensive cooling of the growing crystal, which results in the achievement of a plane crystallization front, contributes to uniform distribution of electrical properties throughout the cross section of the crystal. Grown single crystals which exhibited nonuniform crosssectional distribution of  $\varphi$  were subjected to heat treatment in order to bring about a redistribution of  $\varphi$  values; in the process the mean value of resistivity remained unaltered, while the diffusion-path length of the minority current carriers increased somewhat. 1. Germanium--Processing 2. Germanium--Crystallization 3. Single crystals--Growth 4. Single crystals--Properties I.S. **Card 3/3** 



5/576/61/000/000/006/020 E132/E135

**AUTHORS:** 

Voronov, B.K., Dashevskiy, M. Ya., Titova, E.M., and

Khvostikova, V.D.

TITLE

Obtaining uniform single crystals of semiconductors

by Czochralski's method

SOURCE:

Soveshchaniye po poluprovodnikovym materialam, 4th. Voprosy metallurgii i fiziki poluprovodnikov; poluprovodnikovyye soyedineniya i tverdyye splavy. Trudy soveshchaniya. Moscow, Izd.-vo AN SSSR, 1961.

Akademiya nauk SSSR. Institut metallurgii imeni

A.A. Baykova. Fiziko-tekhnicheskiy institut.

The problem in growing crystals for electrical TEXT: purposes is not now just one of purity but of distributing a controlled impurity in a uniform way. Experimentally this is done by making the crucible in the form of two communicating vessels (Fig.1). Generally the inner vessel contains the impurity in the desired concentration and the outer contains the material, either pure, or with a selected reduced concentration of impurity. connecting aperture is made so small that diffusion of the Card 1/3

的分别,我们在我们的人们的身份的,我们就是这种的,我们就是我们的人,我们就是这个人,我们就是这个人,我们就是这个人,我们就是这个人,我们就是这个人,我们就是这个

5/576/61/000/000/006/020 Obtaining uniform single crystals ... E132/E135

impurity from the inner vessel to the outer can be neglected; the flow in of new material thus takes place only when the crystal is withdrawn from the melt. The concentration of the impurity in the inner vessel can thus be kept up by feeding it into the outer. Formulae are then derived relating the geometrical dimensions of the inner and outer vessels and a specimen calculation is given for designing a crucible for growing an alloyed single crystal. If the distribution of impurity in the crystalline rod drawn out of the crucible is to be non-uniform then this can be arranged by making the cross-sectional area of the outer vessel vary appropriately with depth. There are 2 figures and 12 references: 3 Soviet-bloc and 9 non-

Soviet-bloc. The four most recent English language references are:

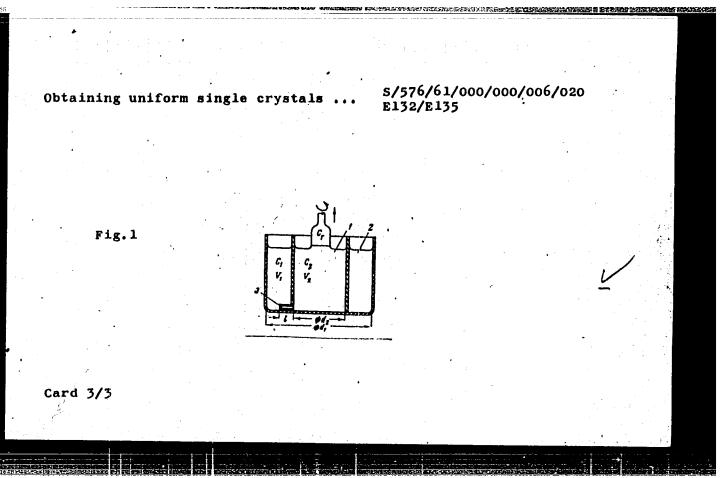
Ref. 4: W. Leverton, J. Appl. Phys., 1958, V. 29, 1241-1242.

Ref. 5: W. Leverton, J. Electrochem. Soc., 1958, 12.

Ref. 7: Nelson. Transistors, 1956, Vol. 1, publ. RCA Laboratories.

Ref. 9; W. Pfann, J. Hobsteller, G. Indig. J. Appl. Phys., 1958, Vol. 29, 1238-1240.

Card 2/3



#### 5/728/61/007/000/001/002

AUTHORS: Annayev, R. G., Allanazarov, A., Manayev, S., Mikhaylov, A. R.,

Dashevskiy, M. Ya., Kafiyev, E. I., Myndyyev, V.

TITLE: Investigation of magnetoelectric properties of n- and p-type ger-

manium single crystals along the principal crystallographic axes.

SOURCE: Akademiya nauk Turkmenskoy SSR. Fiziko-tekhnicheskiy institut.

Trudy, v. 7. /shkhabad, 1961. 3 - 34.

TEXT: Experiments were performed to detect the presence of simple anisotropy in single-crystal germarium with respect to the Hall and Nernst effects, the presence of bianisotropy with respect to the Thomson-Bakhmet'yev thermomagnetic effect, the Thomson-Goldhammer galvanomagnetic effect, and magnetostriction. Along with the foregoing, a check was made on the presence of anisotropy with respect to the thermoment and electric conductivity in a semiconducting germanium crystal as a cubic system, along the principal crystallographic axes, although such anisotropy has not been hitherto observed in metallic cubic-crystal systems. No previous research on this subject is known. At weak fields the galvanomagnetic effect is proportional to the square of the magnetic field intensity, and its magnitude depends on the orientations of the current and of Card 1/3

Investigation of magnitoelectric...

S/728/61/007/000/001/002

the magnetic field vertors relative to the crystallographic axes of the specimen. Longitudinal (current parallel to field) and transverse (current perpendicular to field) galvanomagnetic effects were investigated for a spherical specimen, relative to the [001], [110], and [111] axes in one diagonal plane (110) of the crystal. It is theoretically predicted that the longitudinal effect should be respectively 2.5 and 3 times larger along [110] and [111] than along [001]. The transverse effects are equal for [001] and [110] but not of the same value as for [111], according to theory. The experimental test procedure and the method of crystal production are described. The test results confirm the theory in first approximation only, the presence of bianisotr-py in n-type germanium, and the fact that the absolute values of the galvanomagnetic effect are different along the principal crystallographic axes of n- and p-type germanium crystals. A brief historical summary is presented of studies of the Nernst and Hall effects in semiconductors. Although theory predicts that these effects should be the same along all axes not only for metals but also for semiconductors, no experiments were made heretofore on the latter. This was now confirmed with the same spherical n-type single crystal of germanium as used for the Thomson-Goldhammer effect. A special DC potentiometer developed for this purpose is described. Single crystals of germanium with different types of conductivity were also grown to check on the Card 2/3

Investigation of magneticlectric ...

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course of the "odd" effects in different types of semiconductors. It was found that different impurities give rise to different types of anisotropy. Magnetostriction of single crystals of germanium in fields up to 17,340 Oersted was found to be independent of the directions of the crystal axes and of the measurements, to have a negative sign and to be of the volume type, and to be independent of the type of conductivity. The thermomagnetic Thomson-Bakhmet'yev effect (sometimes called the longitudinal Nernst-Ettinghausen effect) was likewise investigated, using the same specimen and a 17,000 Oersted field, at room temperature, and the germanium crystal was found to be bianisotropic with respect to the longitudinal and transverse thermomagnetic effects, with anisotropic thermal emf and electric resistivity along the principal crystal axes. English papers cited are by Pearson and Suhl (Phys. Rev. vol. 83, 768, 1951), Seitz (Phys. Rev. vol 79, 372, 1950), Morin and Maita (Phys. Rev. vol. 94, 1525, 1954), and Hung and Glissman (Phys. Rev. vol. 96, 1226, 1954). There are 19 figures and 4 tables.

Card 3/3

DASHEVSKIY, M.Ya.; TITOVA, E.M.; KHVOSTIKOVA, V.D.

Chokhal'skii's method of growing single crystals with a uniform distribution of impurities. Trudy Inst. met. no.8:143-148 '61.

(MIRA 14:10)

(Crystals—Growth)

s/020/62/146/004/010/015 B101/B186

AUTHORS:

Lazarev, V. B., Dashevskiy, M. Ya.

. TITLE:

Surface tension of indium - antimony melts

Akademiya nauk SSSR. Doklady, v. 146, no. 4, 1962, 822-825 PERIODICAL:

TEXT: The surface tension of 28 In - Sb melts of various concentrations was neasured range of 550 - 700°C for the following purposes: (1) to find out whether a singular point in the diagram of surface tension versus composition corresponds to the singular point in the phase diagram of a given system in which congruently melting InSb is formed, and (2) to obtain data on the surface tension of melts with a non-stoichiometric composition, -such data being of practical importance in pulling InSb single crystals. The authors prepared the specimens according to Czochralski's method. The surface tension o was determined from the maximum pressure of a gas bubble. . The wall of the quartz capillary was ground to a thickness of 0.01 mm to facilitate calculation of o. The measurement was conducted in an atmosphere of argon at approximately 100 mm Hg with a maximum total error of 1.2 %, corresponding to ~7.0 dyne/cm. Results: on is in good agreement Card 1/3

S/020/62/146/004/010/015 B101/B186

Surface tension of indium - ...

with the data obtained up to  $500^{\circ}$ C by D. A. Melford and T. P. Hoar (J. Inst. Met., 85, no. 5, 197 (1956 - 1957)), O. A. Timofeyevicheva and P. P. Pugachevich (DAN, 124, 1093 (1959)). The authors were the first to measure of the between 500 and  $800^{\circ}$ C. Between 650 and  $800^{\circ}$ C, os was consistent with the data by L. L. Bircumshaw (Phil. Mag. 17, 181 (1934)). In the experiments covering the whole temperature range of melts, antimony was surface-active toward indium. The surface tension of InSb was  $425 \pm 20$  dyne/cm. The curve of versus melt composition shows a singular point at In: Sb = 1:1 \( \subseteq \subseteq = -(C/RT)(1 - C)(\partial \sigma/\partial C) \) [1/(1 + \partial \text{ln f}/\partial \text{ln f}/\partial \text{ln coefficient} and \( \subseteq \subseteq \subseteq \text{ln melts} \) In There are 4 figures.

ASSOCIATION: Institut metallurgii im. A. A. Baykova (Institute of Metallurgy imeni A. A. Baykov). Institut obshchey i neorganicheskoy khimii im. N. S. Kurnakova Akademii nauk SSSR (Institute of General and Inorganic Chemistry imeni N. S. Kurnakov of the Academy of Sciences USSR)

Card 2/3

S/020/62/146/004/010/015
Surface tonsion of indium - ... B101/B186

PRESENTED: May 20, 1962, by I. I. Chernyayev, Academician

SUEMITTED: May 20, 1962

ACCESSION NR: AT4030798

8/0000/63/000/000/0125/0132

AUTHOR: Lamarev, V. B.; Dashevskiy, M. Ya.

TITLE: A study of surface phenomena in melts of the In-Sb system

SOURCE: AN UkrSSR. Institut metallokoramiki i spetsial nywkh splavov. Poverkhnostny\*ye yavleniya v rasplavakh i protsessakh poroshkovoy metallurgii (surface phenomena in liquid metals and processes in powder metallurgy). Kiev, Izd-vo AN UkrSSR, 1963, 125-132

TOPIC TAGS: surface phenomenon, indium, antimony, indium based alloy, antimony containing alloy, surface tension, indium antimonide

ABSTRACT: In this paper the authors presented the results of an investigation of the concentration and temperature relationships of the surface tension of indiumantimony system melts with the congruently melted chemical compound indium antimonide. It was explained that a correspondence exists between the spatial points on the structural diagram of the indiumantimony system and on the diagram surface tension-composition. In addition, experimental data was obtained on the surface tension of melts for which the composition does not strongly differ from the stoichiometric melt of the indiumantimonide compound. A diagram of the instrument

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ACCESSION NR: AT4030798

for determining the surface tension was presented. Results were presented in graphs. The temperature relationship of the surface tension was studied as the following: indium (at a temperature range of 200-800°C), antimony (at a temperature range of 650-800°C) and 26 alloys of the indium-antimony system at a temperature range of 550-700°C. It was established that throughout the entire investigated temperature range, antimony is surface active in relation to indium. It was shown that the existence of an intermetallic compound in the indium-antimony system finds representation in the isotherms of the surface tension in the melts of this system. Orig. art. has: 6 figures and 2 formulas.

ASSOCIATION: Institut obshchey i neorganicheskoy khimii AN SSSR, . Moscow (Institute of General and Inorganic Chemistry, AN SSSR).

SUBMITTED: 23Nov63

DATE ACQ: 16Apr64

ENCL:

SUB CODE: ML

NO REF SOV: 012

OTHER: 008

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ACCESSION NR: AP30005	16 s/0020/63/15	50/002/0297/0300 56
AUTHOR: Dashevskiy, M	Ye. P Mirgalovskaya, M. S.	
TITLE: Some structura	peculiarities of indium antimonide of	lendrites
SOURCE: AN SSSR. Dok	lady, v. 150, no. 2, 1963, 297-300	
TOPIC TAGS: indium an	timonide dendrites, crystal structure,	, twin orystels
ABSTRACT: The indium	entimonide dendrites studies were grown a melt cooled 7-10 degrees below cry	m by vertical pulling
seeding with crystals	oriented in one of the [211] direction types of structures of these twin-crys	s. A detailed des-
conclusion the authors	express thanks to N. Ye. Il'in for as of the work. Orig. art. has: 4 figur	ssistance in conducting
ASSOCIATION: Institut	metallurgii im. A. A. Baykova (Instit	tute of Metallurgy)
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ſ	L 47338.66 EWT(1)/EWI(m)/T/EWP(t)/ETI 1JP(c) GG/WW/GG/17  ACC NR: AR6025717 SOURCE CODE: UR/0058/66/000/004/A071/A071	
	AUTHOR: Dashevskiy, M. Ya.  TITLE: Some problems in obtaining crystals with specified distribution of impurities	
	by growing from the melt	
	SOURCE: Ref. zh. Fizika, Abs. 4A600 REF SOURCE: Sb. Simpozium. Protsessy sinteza i rosta kristallov i plenok poluprovod-	
1	nik. materialov, 1965. Tezisy dokl. Novosibirsk, 1905, 9	
	TOPIC TAGS: single crystal growing, crystal impurity, dendrite, crystal lattice structure	
	ABSTRACT: The author considers possible causes of microhomogeneous and macroinhomogeneous distribution of impurities in single crystals grown from the melt by the Czoch ralski method, and then discusses methods of obtaining single crystals with homogene-	100
	ous or specified impurity distribution. The author considers the distribution of purities in ribbon-type dendrites of substances that crystallize in a diamond lattice; purities in ribbon-type dendrites of substances that crystallize in a diamond lattice;	
	drawing from the melt, and discusses the distribution of impurities and the structure of the dendrite. [Translation of abstract]	17
	SUB CODE: 20	2
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AUTHOR: Lazarev, V. B   Dashevakiy, M. Y	3	
TITLE: Surface tension of fusions of gen	manium-antimony and germanium-nickel	
	mittan-difficant and Selmanian-Dickel	
SOURCE: AN SSSR. Izvestiya. Seriya khimi	heskava no 1 1065 170-172	T.
TOPIC TAGS: germanium, antimony, nickel.	germanium alloy, surface tension	
ABSTRACT: The surface tension of germani	m-antimony and germanium-nickel melts was	
measured and the adsorption of antimony of	the germanium surface was calculated	1.
kerationships were found between the solu	illty and distribution ratios of the	
dopants and hetween the dopant solubility	and the surface tensions of solvent and	
additive. Orig. art. has: 2 tables, 2 f	21Pes	
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ASSOCIATION: Institut obshchey i neorgan Akademii nauk SSSR (Institute of General Sciences SSSR)  SUBMITTED: 26May64 ENC	cheskoy khimii im. N. S. Kurnakova and Inorganic Chemistry. Academy of SUB CODE: MM. IC	
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L'11001-66 EWI (11)/EWP(t)/EWP(b) LJP(c) ACC NR: AP5028720 SOURCE CODE: UR/0363/65/001/011/1901/1910 **AUTHOR:** Lazarev, V. B.; Dashevskiy, H. Ya. ORG: Institute of Gineral and Inorganic Chemistry im. N. S. Kurnakov, Academy of Sciences SSSR (Institut obshchey i neorganicheskoy khimii Akademii nauk SSSR); Institute of Metallurgy im. A. A. Baykov (Institut metallurgii) 55 TITLE: Surface phenomena and crystallization processes in doped indium antimonics al loys SOURCE: AN SSSR. Izwestiya. Neorganicheskiye materialy, v. 1, no. 11, 1965, 1901--1910 TOPIC TAGS: indiam compound, satimonide, selenium, tellurium, germanium, surface tension, chemical absorption, metal crystallization, alloy, crystal growth 27,53 ABSTRACT: The effect: of selenium, tellurium, and germanium on the surface tension of indium antimonide melts was studied, and it was shown that Se and Te are absorbed at the interface, whereas practically no absorption of germanium occurs. Differences in the growth of indium antimonide dendrites from melts doped respectively with Se and Te are due to the different absorbability of these substances on indium antimonide. A new method is proposed for estimating the effective generalized moments of elements and compounds, and it is shown that the structure of melts can be evaluated UDC: 546.682'861:532.6

by using data on their is suggested that the characterize the diffitween the solubility sion constants and the are presented. In continuous and particip y. Pershikov for assitables, 4 formulas.	difference in the of impurities difference mclusion, the atton in the	n the surface ir molecular , coefficient in the surface authors than discussion of	tension of two s force fields. The s of their distri- te tension of the ak H. S. Mirgalovs the results, and	ubstances be used to relationships be- bution, and diffu- solvent and additive the solvent and additive the solvent and additive the solvent and the solvent a	re med
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LAZAREV, V.B.; DASHEVSKIY, M.Ya.

Surface phenomena and crystallization processes in alloyed indium antimonide melts. Izv. AN SSSR. Neorg. mat. 1 no.11:1901-1910 N 165. (MIRA 18:12)

1. Institut obshchey i neorganicheskoy khimii imeni N.S. Kurnakova AN SSSR i Institut metallurgii imeni A.A. Baykova. Submitted July 5, 1965.

ACC NR: AR6035419

SOURCE CODE: UR/0137/66/000/009/C052/C052

AUTHOR: Dashevskiy, M. Ya.; Mirgalovskaya, M. S.; Lazarev, V. B.

TITIE: Growing of indium antimonide crystals from melts doped with surface-active and surface-inactive additives

SOURCE: Ref. zh. Metallurgiya, Abs. 9G364

REF SOURCE: Sb. Poverkhnostn. yavleniya v rasplavakh i voznikayushchikh iz nikh tverd fazakh. Nal'chik, 1965, 579-584

TOPIC TAGS: indium compound, antimonide, surface active agent, single crystal growing, surface tension, dendrite

ABSTRACT: A description is presented of a combined setup for growing of single crystals drawn from the melt and measuring the surface tension of the melt. Measurement of the surface tension of a melt of InSb doped with Ge or Se has shown that the Se is surface-active (it is adsorbed) while the Ge is surface-inactive (is not adsorbed) as an additive. Single crystals and dendrites of InSb were drawn from melts doped with germanium in the range 0.05 - 2.5 at.% and Se 0.024 - 0.25 at.%. With increasing Ge concentration in the melt, the width of the dendrite ribbons decreased. No noticeable influence of Ge on the growth of the single crystal was noted. Dendrites with large Si content could not be grown, for their growth stopped at 0.25 at.% Se. No morphological differences were noted between single crystals grown from melts alloyed with Se or Ge. The dependence of the supercooling of the InSb melt on the Ge or Se con-

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ACC NRI AR7000837

SOURCE CODE: UR/0058/66/000/009/A049/A049

AUTHOR: Dashevskiy, M. Ya.; Mirgalovskaya, M. S.; Lazarev, V. B.

TITLE: Growing single indium antimonide crystals from melts doped with surface-active and surface-inactive impurities

SOURCE: Ref. zh. Fizika, Abs. 9A415

REF SOURCE: Sb. Poverkhnostn. yavleniya v rasplavakh i voznikayushchikh iz nikh tverd. fazakh. Nal'chik, 1965, 579-584

TOPIC TAGS: crystal, crystal growth, crystal impurity, indium antimonide, crystallography, surface active alloy, surface inactive alloy, surface active impurity, surface inactive impurity, impurity, semiconductor crystal, germanium alloy, selenium alloy, doping

ABSTRACT: A description is given of a device for growing monocrystals (C) by pulling them from a melt (M), and for measuring surface tension of M. Measurements of surface tension of M in InSb doped with Ge and Se showed that Se is a surface-active impurity, and that Ge is a surface-inactive impurity. Monocrystals

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2 E at the and w	837 from M [sec] were gro ith Se in the amount of	f 0, 0024 — 0, 25 at %.	An increase in	THE COIL
centration of C	le in the M was accomp	anied by a decrease in the growth of C was in	n the width of d noted. No succ	ess was
- alei accord in an	owing dendrites contain	ing large amounts or	se, since at o.	20 at /v ] ·
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and a sharms the	t within the given range ercooling only slightly	of concentrations. U	e and be affect	ict]
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ACC NR: AP7005591

BOURCE CODE: UR/0020/67/172/002/0403/0406

AUTHOR: Dashovskiy, M. Ta: Kukuladze, G. V.; Lazarev, V. B.; Mirgalovskaya, M. S.

ORG: Metallurgy Institute im. A. A. Baykov, Academy of Sciences, SSSR (Institut metallurgii Akademii nauk SSSR); Institute of General and Inorganic Chemistry im. N. S. Kurnakov, Academy of Sciences, SSSR (Institut obshchey i neorganicheskoy khimii Akademii nauk SSSR)

TITIE: Surface phenomena and crystallization processes in gallium antimonide melts

SOURCE: AN SSSR. Doklady, v. 172, no. 2, 1967, 403-406

TOPIC TAGS: surface tension, gallium compound, antimonide, crystallization

ABSTRACT: In order to determine the general applicability of the regularities characterizing the relationship between surface phenomena and crystallization processes in indium antimonide melts, the following phenomena were investigated: surface tension of melts of the gallium-antimony system, influence of zinc and tellurium on the surface tension of gallium antimonide, and influence of these admixtures on the supercooling of Ga-Sb melts and on the growth of crystals from the melts. It is suggested that the behavior of the impurities in the solvent melt can be predicted from the difference of surface tensions in the case of type AIIISb antimonides. In AIIIBV compounds which crystallize in a zinc-blende-type lattice, a correlation exists between the mean atomic number of the compound and the surface tension at the

Card 1/2

VDC: 546.682'861:532.6

### ACC NR: AP7005591

melting point: the higher the mean atomic number, the lower the surface tension of the compound. Data on the effect of Te on the supercooling of indium antimonide indicate that surface-active admixtures increase the probability of formation of a solid phase nucleus. At a certain concentration of Te, the growth of lamellar dendrites of gallium antimonide was hindered, causing distorted dendrites to grow, then was stopped altogether as the Te content increased further. The introduction of zinc in appreciable amounts did not interfere with the growth of lamellar dendrites of gallium antimonide. The regularities found by studying the role of surface phenomena in the crystallization of indium antimonide melts were found to apply to gallium antimonide as well, and are therefore thought to cover at least all compounds of type AIIIBV which crystallize in a zinc-blende-type lattice. The paper was presented by Academician Sazhin, N. P., 4 Apr 66. Orig. art. has 3 figures and 1 table.

SUB CODE: 11,20/ SUBH DATE: 04Apr66/ ORIG REF: 009/ OTH REF: 001

2/2